REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the pending application. The Final Office Action dated February 17, 2006 has been received and its contents carefully reviewed.

Claims 1 and 9 are hereby amended, and claims 2 and 10 are canceled. Accordingly, claims 1, 3–9, and 11–12 are currently pending, with claims 5–8 being withdrawn from consideration. Reexamination and reconsideration of the pending claims are respectfully requested.

In the Office Action, claims 1, 2, 4, 9, 10, and 12 are rejected under 35 U.S.C. § 102(b) as being anticipated by U.S. Patent No. 6,726,802 to Ono et al. (hereinafter "Ono"); and claims 3 and 11 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Ono.

In the Office Action, claims 1, 2, 4, 9, 10, and 12 are rejected under 35 U.S.C. § 102(b) as being anticipated by Ono. Applicants respectfully traverse the rejection of independent claim 1 and request reconsideration. Independent claim 1 is allowable in that it recites "a storage capacitor having a lower storage electrode across the data line and in parallel with the gate line on the same layer as the gate line, wherein the lower storage electrode divides the pixel region into two sub-regions, and a semiconductor layer interposed between the lower storage electrode and the pixel electrode, wherein the pixel electrode is connected to the semiconductor layer by a through hole formed on an upper region of the semiconductor layer." Nothing in Ono teaches or suggests at least this feature of the claimed invention.

The Examiner cites FIG. 17 of Ono as teaching "a storage capacitor having a lower storage electrode across the data line and in parallel with the gate line on the same layer as the gate line, wherein the lower storage electrode divides the pixel region into two sub-regions, and a semiconductor layer interposed between the lower storage electrode and the pixel electrode," (Office Action, p. 2) and FIG. 21 as teaching "wherein the pixel electrode is connected to the semiconductor layer by a through hole formed on an upper region of the semiconductor layer." (Office Action, p. 3). Applicants respectfully assert that FIGs. 17 and 21 pertain to different embodiments of the invention, and that the above feature of claim 1 is not taught by either embodiment. In order to have anticipation under 35 U.S.C. § 102, "[t]he identical invention

must be shown in as complete detail as is contained in the ... claim." (MPEP 2131). Further, "[t]he elements must be arranged as required by the claim." (Id.) Applicants respectfully assert that Ono fails to show the above feature of claim 1 as arranged according to the claim, and that Ono fails to anticipate the claimed invention.

The embodiment illustrated in FIG. 21 is also illustrated in FIG. 19. (Embodiment 5, col. 23, ll. 13–14). This embodiment, which the Examiner cites as teaching "wherein the pixel electrode is connected to the semiconductor layer by a through hole formed on an upper region of the semiconductor layer," does not show the "a-Si channel film AS" and the "common electrode wiring line CT" dividing the pixel region into two sub-regions. In contrast, FIG. 19 shows the a-Si channel film at one edge of the pixel region.

Accordingly, Ono fails to teach or suggest "a storage capacitor having a lower storage electrode across the data line and in parallel with the gate line on the same layer as the gate line, wherein the lower storage electrode divides the pixel region into two sub-regions, and a semiconductor layer interposed between the lower storage electrode and the pixel electrode, wherein the pixel electrode is connected to the semiconductor layer by a through hole formed on an upper region of the semiconductor layer." As such, Applicants respectfully submit that claim 1, and its dependent claim 4, are allowable over Ono.

Applicants respectfully traverse the rejection of independent claim 9 and request reconsideration. Independent claim 9 is allowable in that it recites "a semiconductor layer on the lower storage electrode ... wherein the lower storage electrode is parallel to the gate line and divides the pixel region into two sub-regions, and wherein the pixel electrode is connected to the semiconductor layer by the through hole above the semiconductor layer." Nothing in Ono teaches or suggests at least this feature of the claimed invention. Accordingly, for the same or similar reasons as those pertaining to claim 1 above, Applicants respectfully submit that claim 9, and its dependent claim 12, are allowable over Ono.

In the Office Action, claims 3 and 11 are rejected under 35 U.S.C. § 103(a) as being unpatentable over Ono. Applicants respectfully traverse the rejection of claim 3 and request reconsideration. Claim 3, which depends from independent claim 1, is allowable because Ono

fails to teach or suggest every element of claim 1, as discussed above. Accordingly, Applicants respectfully submit that claim 3, as it depends from independent claim 1, is allowable over Ono.

Applicants respectfully traverse the rejection of claim 11 and request reconsideration. Claim 11, which depends from independent claim 9, is allowable because Ono fails to teach or suggest every element of claim 9, as discussed above. Accordingly, Applicants respectfully submit that claim 11, as it depends from independent claim 9, is allowable over Ono.

Applicants believe the foregoing amendments place the application in condition for allowance and early, favorable action is respectfully solicited.

If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at (202) 496-7500 to discuss the steps necessary for placing the application in condition for allowance. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. A duplicate copy of this sheet is enclosed.

Dated: May 17, 2006

Respectfully submitted,

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